

INTERNATIONAL STANDARD ISO/IEC 14443-2:2020 TECHNICAL CORRIGENDUM 2

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Cards and security devices for personal identification — Contactless proximity objects — Part 2: Radio frequency power and signal interface

TECHNICAL CORRIGENDUM 2

Cartes et dispositifs de sécurité pour l'identification personnelle — Objets sans contact de proximité — Partie 2: Interface radiofréquence et des signaux de communication

RECTIFICATIF TECHNIQUE 2

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Page 25, 8.2.2.3

Replace all of the text in the subclause before Figure 13 by the following:

For each subcarrier period:

- \mathcal{O}_{LM} is defined as the argument of all differences between sections in the occurrence of MS1 and the corresponding sections in the occurrence of MS2 in the same subcarrier period, as illustrated in Figure 13;
- there is an absolute maximum and an absolute minimum of \mathscr{O}_{LM} ; \mathscr{O}'_{LM} is defined as the one which occurs first in time, \mathscr{O}''_{LM} is the one which occurs secondly, then

 $\Delta \mathscr{O}_{\rm LM} = \mathscr{O}''_{\rm LM} - \mathscr{O}'_{\rm LM};$

— with $\mathscr{O}_{\text{LM-left}}$ being the maximum absolute difference between \mathscr{O}'_{LM} and any \mathscr{O}_{LM} occurring before \mathscr{O}'_{LM} in time and $\mathscr{O}_{\text{LM-right}}$ being the maximum absolute difference between $\mathscr{O}''_{\text{LM}}$ and any \mathscr{O}_{LM} occurring after $\mathscr{O}''_{\text{LM}}$ in time

 $\mathscr{O}_{\text{LMsecond}} = \max(\mathscr{O}_{\text{LM-left}}; \mathscr{O}_{\text{LM-right}});$

- if $(\mathcal{O}_{\text{LMsecond}} / \text{abs}(\Delta \mathcal{O}_{\text{LM}})) > 0.8$ then $\Delta \mathcal{O}_{\text{LM-E}}$ is defined as the absolute maximum phase variation and $\Delta \mathcal{O}_{\text{LM}}$ is set to 0; else $\Delta \mathcal{O}_{\text{LM}}$ is defined as the signed maximum phase variation and $\Delta \mathcal{O}_{\text{LM-E}}$ is set to 0.

Figure 14 illustrates \mathscr{O}_{LM} , \mathscr{O}'_{LM} , \mathscr{O}''_{LM} , $\mathscr{A}\mathscr{O}_{LM}$, $\mathscr{O}_{LMsecond}$ and $\mathscr{A}\mathscr{O}_{LM-E}$.

The intrastate phase drift is defined as:

 $- \mathscr{O}_{LM, INTRA} = \max(\max(\max(\Delta \mathscr{O}_{LM}); 0) - \min(\min(\Delta \mathscr{O}_{LM}); 0); \max(\Delta \mathscr{O}_{LM-E}))$

where max($\Delta \mathcal{O}_{LM}$) and min($\Delta \mathcal{O}_{LM}$) are the maximum and minimum of $\Delta \mathcal{O}_{LM}$ computed over all occurrences of all subcarrier periods, respectively.

Page 26, 8.2.2.3 Replace Figure 14 with the following:



Х	subcarrier cycles (transitions between modulated states are not considered)
Y	
А	Ø′lм
В	ؔlm
С	$\Delta O \!\!\!\!/ M_{ m LM}$
D	$ ot\!\!\!/_{ m LMsecond} $
E	$\Delta {\it p}_{ m LM-E}$

Figure 14 — Time domain plot during part of the PICC response, depicting \mathscr{O}_{LM}

Page 28, 8.2.5.1

Replace Table 24 by the following:

Table 24 — Load modulation amplitude limits for PCD reception

PICC Class	V LMA, min, PCD mV (peak)	V LMA, max, PCD mV (peak)	Subcarrier frequency	Reference PICC	Test PCD assembly
1	20/H ^{0,5}	110 mV	<i>f</i> c/16	Active Reference PICC 1	Test PCD assembly 1
			>fc/16	Reference PICC 1	
2	Min(12,5 ; 20/ <i>H</i> ^{0,5})	100 mV	<i>f</i> c/16	Active Reference PICC 2	Test DCD accomply 1
			<i>>f</i> c/16	Reference PICC 2	Test PCD assembly 1
3	Min(12,5 ; 20/ <i>H</i> ^{0,5})	90 mV	<i>f</i> c/16	Active Reference PICC 3	Test PCD assembly 1
			<i>>f</i> c/16	Reference PICC 3	
4 (optional)	Min(1(2(/105)))	110 m V	<i>f</i> c/16	Active Reference PICC 4	Test DCD accomply 2
	MIII(10; 30/ <i>П</i> ^{0,3})	110 1110	<i>>f</i> c/16	Reference PICC 4	Test PCD assembly 2
5 (optional)	$M_{in}(12, 21/105)$	100 mV	<i>f</i> c/16	Active Reference PICC 5	Test DCD assembly 2
	$\min(13;31/H^{0,3})$	100 mv	<i>>f</i> c/16	Reference PICC 5	rest PCD assembly 2
6 (optional)	Min(6 ; 23/H ^{0,5})	90 mV	<i>f</i> c/16	Active Reference PICC 6	Test DCD assembly 2
			>fc/16	Reference PICC 6	Test PCD assembly 2